EAST SEARCH FOR 10-773,863

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	155	semiconductor adj (exhaust or waste or offgas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT
2	BRS	L2	145018	((high adj temperature) or hot) adj air	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT
3	BRS	L3	4	1 same 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT

	Time Stamp	Comments	Error Definition	Errors
1	2006/11/20 08:49			
2	2006/11/20 08:50			
3	2006/11/20 08:50			

DERWENT-ACC-NO: 2006-327021

DERWENT-WEEK: 200634

TITLE: Method for increasing purification efficiency of exhaust from a semiconductor production process comprises ejecting hot air at the exhaust outlet end in an exhaust treatment tank for directly fully purifying harmful material in the exhaust

INVENTOR: FENG, W

PATENT-ASSIGNEE: ORIENT SERVICE CO LTD[ORIEN]

PRIORITY-DATA: 2003TW-0103924 (February 25, 2003)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 230240 B1	April 1, 2005	N/A	000	F23G 007/06
TW 200416369 A	September 1, 2004	N/A	000	F23G 007/06

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 230240B1	N/A	2003TW-0103924	February 25, 2003
TW 200416369A	N/A	2003TW-0103924	February 25, 2003

INT-CL (IPC): F23G007/06

ABSTRACTED-PUB-NO: TW 200416369A

BASIC-ABSTRACT:

NOVELTY - A method for increasing the purification efficiency of an exhaust from a semiconductor production process mainly comprises:

forcedly ejecting a **hot air** at the exhaust outlet end in an exhaust treatment tank for directly fully purifying harmful material in the exhaust by using the feature where the **hot air** has an optimal catalytic temperature at the outlet end, thereby increasing the purification efficiency of the **semiconductor exhaust**.

CHOSEN-DRAWING: Dwg.0/0

TITLE-TERMS: METHOD INCREASE PURIFICATION EFFICIENCY EXHAUST SEMICONDUCTOR PRODUCE PROCESS COMPRISE EJECT HOT AIR EXHAUST OUTLET END EXHAUST TREAT TANK PURIFICATION HARM MATERIAL EXHAUST

DERWENT-CLASS: Q73

SECONDARY-ACC-NO:

Non-CPI Secondary Accession Numbers: N2006-276818

DERWENT-ACC-NO: 2006-654260

DERWENT-WEEK: 200668

TITLE: Method for cleaning harmful materials of semiconductor waste gas to accelerate chemical reaction of harmful materials included in semiconductor waste gas

INVENTOR: FENG, W N

PATENT-ASSIGNEE: FENG W N[FENGI]

PRIORITY-DATA: 2004KR-0009264 (February 12, 2004)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 2005081035 A	August 18, 2005	N/A	000	H01L 021/02

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR2005081035A	N/A	2004KR-0009264	February 12, 2004

INT-CL (IPC): H01L021/02

ABSTRACTED-PUB-NO: KR2005081035A

BASIC-ABSTRACT:

NOVELTY - A method for cleaning harmful materials of **semiconductor waste** gas is provided to accelerate a chemical reaction of harmful materials included in **semiconductor waste** gas by guiding **high temperature air** to an outlet of waste gas of a semiconductor gas reducing system.

DETAILED DESCRIPTION - **Hot air**(30) is injected into a waste gas outlet(13) of a semiconductor gas reducing system(1). The **hot air** is

sent to **semiconductor waste** gas(4) exhausted from the waste gas outlet to accelerate the reaction of harmful materials in the **semiconductor waste** gas. The **hot air** is generated from a **hot air** generating unit(2).(C) KIPO 2006Image 1/1

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS: METHOD CLEAN HARM MATERIAL SEMICONDUCTOR WASTE GAS ACCELERATE CHEMICAL REACT HARM MATERIAL SEMICONDUCTOR WASTE GAS

DERWENT-CLASS: U11

EPI-CODES: U11-C15Q;